NVMTS2002 PROGRAM

as of *21-Oct* **CLICK ON TITLE FOR ABSTRACT**

NOTE: ORDER and **TITLES** of Presentations *Subject to Change*

MONDAY Nov 4

6PM to 8PM	**Registration Reception** Hibiscus Suite

TUESDAY Nov 5

	8:45 AM	**Introduction & Welcoming Remarks**
[1]	**9:00 AM**	**Keynote Address: The Missions of the Jet Propulsion Laboratory; David Crisp, Jet Propulsion Laboratory**
		Applications K Clark, Jet Propulsion Laboratory, *Chair*
[2]	**9:40 AM**	The Future of NonVolatile Memories; T. Mikolajick, Infineon
[3]	**10:05 AM**	System and Economic Requirements for Advanced Non-Volatile Memories; R. Andrei, Web-Feet Research
	10:30 AM	*BREAK*
[4]	**10:45 AM**	Embedded Memory Technologies - the First Step Towards SoC; R. Andrei, Web-Feet Research
[5]	**11:10 AM**	Rugged & Reliable Data Storage: Choosing the Right Media for Rugged COTS Mass Data Storage; O. Tzur, M-Systems
[6]	**11:35 AM**	High Speed, Radiation Hard MRAM Buffer; R. Sinclair, NVE Corp.
	12:00 PM	***LUNCH***
[7]	**1:00 PM**	**Invited Talk: Remembering the Past from the Depths of Space; K. Clark, Jet Propulsion Laboratory**
		INNOVATIVE CONCEPTS J Zhu, Carnegie-Mellon University, *Chair*
[8]	**1:40 PM**	Compact Holographic Memory Using E-O Beam Steering Technology; T-H Chao, Jet Propulsion Laboratory
[9]	**2:05 PM**	High Performance Organic Non-Volatile Memory Device ---a Direct Challenge to the Si Technology; Y. Yang, University of California at Los Angeles
	2:30 PM	*BREAK*
[10]	**2:45 PM**	The Transpinnor®: An Active Spin-Based Device; E. Torok, Integrated Magnetoelectronics
[11]	**3:10 PM**	Static FRAM: A Novel Ferroelectric Memory Approach; J. Evans, Radiant Technology
[12]	**3:35 PM**	Enabling MLC NAND Flash for Cost-Effective, High Capacity Data Storage; R. Dan, M-Systems
		SPECIAL SESSION: The (New) Flash Phenomenon: Sporadic Extraneous Programming, K Strauss, JPL, *Chair*
[13]	**4:00 PM**	Invited Talk: Inadvertently Programmed Bits in Samsung 128 Mbit Flash Devices - A Flaky Investigation; G. Swift, JPL
[14]	**4:25 PM**	Invited Talk: Description and Reliability of a Robust 0.18 micron Low Voltage and Low Power Embedded Flash Technology; A. Khan, Philips Semiconductor
	4:50 PM	**End of Day**
	5:00 - 7 PM	**Evening Reception, Hibiscus Suite**

WEDNESDAY Nov 6

	8:30 AM	**Reconvening Remarks**
[15]	**8:45 AM**	**Invited Talk: Utilization of Advanced Microelectronics in Space Applications; S. Kayali, Jet Propulsion Laboratory**
		Environment, Reliability, and Modeling K Hunt, AFRL, *Chair*
[16]	**9:25 AM**	Reliability and Endurance of FRAM: A case study; J. Namkung, JPL
[17]	**9:50 AM**	Evaluation of Data Retention and Imprint Characteristics of FRAMs Under Environmental Stresses for NASA Applications; A. Sharma, Goddard Space Flight Center
[18]	**10:15 AM**	Tunneling Phenomenon in SuperFlash® Cell; A. Kotov, Silicon Storage Technology
	10:40 AM	*BREAK*
[19]	**10:55 AM**	Radiation Testing of EEPROM Embedded in a 3 GHz Phase Locked Loop; M. Burgener, Peregrine Semiconductor
[20]	**11:20 AM**	Single Event Effect and Total Ionizing Dose Response of Emerging Non-Volatile Memories; D. Nguyen, Jet Propulsion Laboratory
[21]	**11:45 AM**	Single Event Effect Evaluation of FeRAM Memories for Space Applications; L. Scheick, Jet Propulsion Laboratory
	12:10 PM	***LUNCH***
[22]	**1:10 PM**	**Invited Talk: Non-Volatile Parameters - The Good, The Bad, The Ugly; K. Hunt, AFRL**
		EMERGING TECHNOLOGIES G Derbenwick, Celis Semiconductor, *Chair*
[23]	**1:50 PM**	Integration and Circuit Demonstration of Chalcogenide Memory Elements with a Radiation Hardened CMOS Technology; J. Rodgers, BAE Systems
[24]	**2:15 PM**	Low Power 256K MRAM Design; R. Beech, NVE Corp.
	2:40 PM	*BREAK*
[25]	**2:55 PM**	MRAM Design Limitations Dictated by Thermally Activiated Reversal; J. Zhu, Carnegie Mellon University
[26]	**3:20 PM**	Reproducible Electric-Pulse Induced Resistive (EPIR) Switch Effect of Manganite Films for Non-Volaitle Memory Applications; A. Ignatiev, University of Houston
[27]	**3:45 PM**	High Density NDRO Ferroelectric Memory; D. Kamp, Celis Semiconductor
[28]	**4:10 PM**	Nonvolatile and SDRAM Ferroelectric Memories for Space Applications; D. Kamp, Celis Semiconductor
[29]	**4:35 PM**	FRAM: Advanced Feature Set Pulls the Technology into the High Density Domain; T. Davenport, Ramtron
	5:00 PM	**END of SYMPOSIUM**